



Question Paper Code:

EC301ES

ACE-R20

Semester End Examination II B. Tech- I Semester- MARCH-2022 ANALOG AND DIGITAL ELECTRONICS (Common to CSE, IT)

Time: 3 Hours	5	Max. Marks: 70	
H. T. No			

Answer any 5 Questions out of 8 Questions from the following

Q.No	Question	Marks
1. a)	Explain the operation of silicon p-n junction diode and obtain the forward and	
	reverse bias V-I characteristics.	
b)	Define Diffusion capacitance? Also derive the expression for C _D ?	
2. a)	Draw and explain the V-I characteristics of a tunnel diode.	6
b)	Explain the working of a half wave rectifier with necessary waveforms.	8
3. a)	Discuss about thermal run away and thermal stability.	4
b)	Explain the input and output characteristics of common base configuration.	10
4. a)	Compare CB, CE and CC transistor configurations.	5
b)	Explain compensation techniques with respect to BJT biasing.	9
5. a)	Write the differences between BJT and FET.	5
b)	Describe the operations of all logic gates with an example.	9
	Express the following function into sum of min terms and product of max	7
	terms. $F(A,B,C,D)=B'D+A'D+BD$	
b)	Simplify the following Boolean function using 4-variable K-map.	7
	$F(w,x,y,z) = \sum (1,3,7,11,15) + \sum d(0,2,5)$	
7. a)	Draw the logic diagram of 8x1 multiplexer and explain its operation.	7
b)	Draw the truth table of SR flip-flop and obtain its characteristic equation.	7
8.	Explain in detail about 3-bit ripple counter with neat diagram.	14